

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-7 (canceled)

Claim 8 (currently amended) A method for producing a gallium nitride-based compound semiconductor light-emitting device comprising providing an n-type layer and a light-emitting layer each comprising a gallium nitride-based compound semiconductor, providing a p-type layer comprising a gallium nitride-based compound semiconductor through the following steps:

producing a gallium nitride-based compound semiconductor layer doped with a p-type impurity;

producing a catalyst layer of a monolayer or multilayer film having thickness of 1 to 100 nm comprising a metal, alloy or metallic compound containing Ni ~~at least one element selected from the group consisting of Ni, Co, Fe, Mn, Cr, V, Ti, Re, W, Ta, Hf, Lu, Gd, Ce, La, Ru, Mo, Zr, Y, Au, Ag, Cu, Al and Bi~~ on said gallium nitride-compound semiconductor layer;

annealing the gallium nitride-based compound semiconductor layer fixed with said catalyst layer in an atmosphere gas containing no oxygen at a temperature of 200 to 600° C;

stripping said catalyst layer completely; and

providing a p-side electrode on said p-type layer after annealing.

Claims 9-13 (canceled)